

SANYO Semiconductors DATA SHEET

MCH3421—

N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		100	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		0.8	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	3.2	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Llmit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =400mA	0.5	1.0		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =400mA, V _{GS} =10V		0.68	0.89	Ω
	RDS(on)2	ID=400mA, VGS=4V		0.85	1.2	Ω
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		165		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		13		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		8.0		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		7		ns
Rise Time	t _r	See specified Test Circuit.		3		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		22		ns
Fall Time	tf	See specified Test Circuit.		10		ns

Marking: KW Continued on next page.

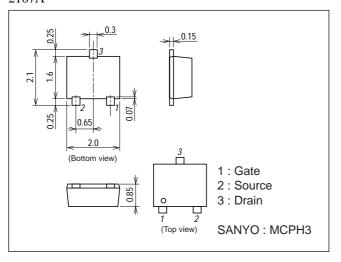
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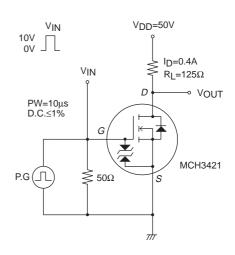
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Total Gate Charge	Qg	V _{DS} =50V, V _{GS} =10V, I _D =0.8A		4.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =50V, V _{GS} =10V, I _D =0.8A		0.9		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =50V, V _{GS} =10V, I _D =0.8A		0.9		nC
Diode Forward Voltage	VSD	IS=0.8A, VGS=0		0.86	1.2	V

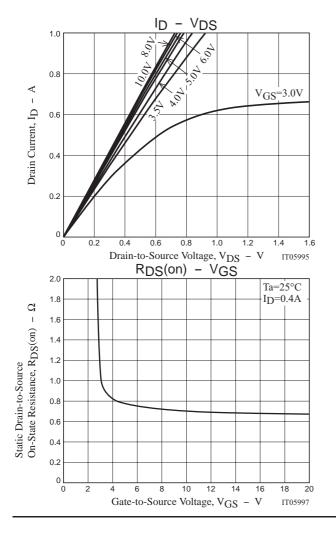
Package Dimensions

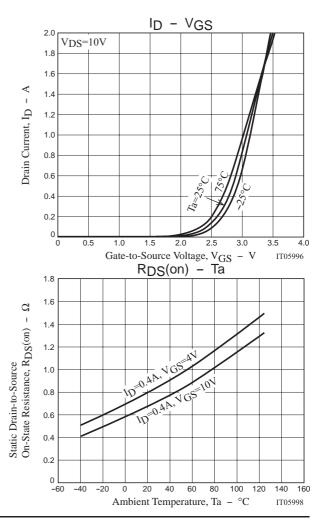
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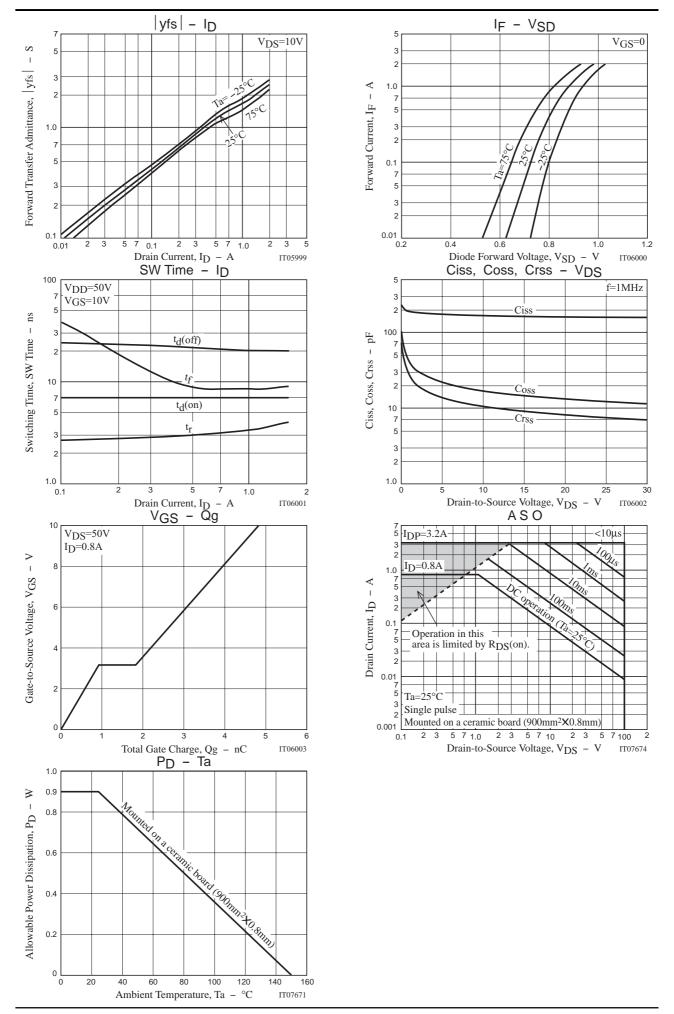


Switching Time Test Circuit









Note on usage: Since the MCH3421 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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